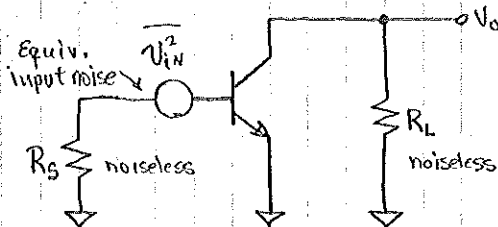


## Equivalent Noise & Minimum Detectable signal

- Noise is affected by the circuit gain
- For meaningful comparisons, sources are expressed in terms of an equivalent input noise signal
- This is a source that would produce the same output noise as the circuit in consideration.



$$\overline{V_o^2} = g_m^2 R_L^2 \frac{|Z|^2}{|Z + r_b + R_S|^2} \overline{V_{IN}^2}$$

Therefore

$$\overline{V_{IN}^2} = 4KT(R_S + r_b) + (R_S + r_b)^2 2qI_B + \frac{1}{g_m^2 R_L^2} \frac{|Z + r_b + R_S|^2}{|Z|^2} R_L^2 \left( 4KT \frac{1}{R_L} + 2qI_C \right)$$

Example:

Input noise in circuit CE. for 0-1MHz b.w.

Using the total output noise

$$A_v = \frac{r_{\pi}}{r_b + r_{\pi} + R_S} g_m R_L = \frac{26000}{200 + 26000 + 500} \cdot \frac{5000}{260} = 18.7$$

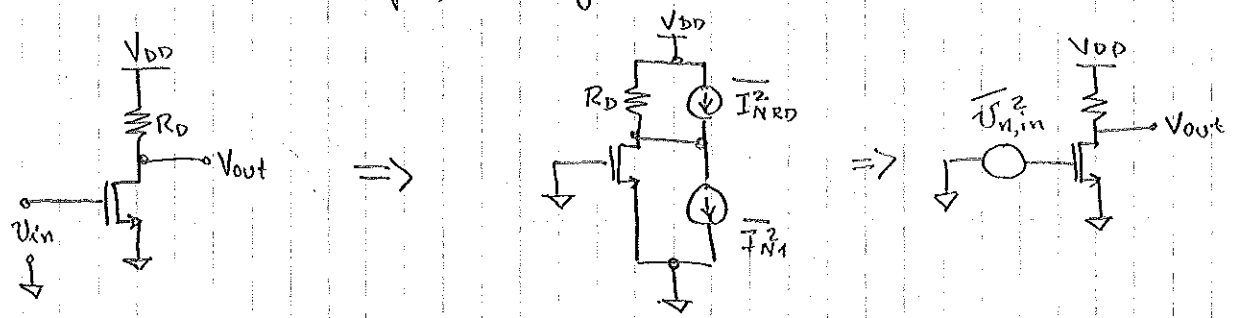
$$\text{Flat spectrum @ 1MHz } \overline{V_{in}^2} = \frac{\overline{V_{out}^2}}{A_v^2} = \frac{5 \times 10^9}{(18.7)^2} = 14.3 \times 10^{12} \text{ V}^2$$

$$V_{inT, \text{rms}} = \sqrt{\overline{V_{in}^2}} = 3.78 \mu\text{V}$$

This level is the minimum detectable signal for the circuit

Another example:

A common source amplifier stage



$$\overline{I_{NRD}^2} = \underbrace{4KT/R_D}_{\text{Thermal } R_D}$$

$$\overline{I_{N1}^2} = \underbrace{4KT \left(\frac{2}{3}\right) g_m}_{\text{channel Thermal}} + \underbrace{K_1 g_m^2 \frac{1}{C_{ox} W L f}}_{\text{Flicker}}$$

$$\overline{V_{n,out}^2} = \left( 4KT \left(\frac{2}{3}\right) g_m + \frac{K_1}{C_{ox} W L} \cdot \frac{1}{f} g_m^2 + \frac{4KT}{R_D} \right) R_D^2$$

The equivalent input noise: From 3rd circuit  $\overline{V_{n,out}^2} = \overline{V_{n,in}^2} \cdot A_v^2$

$$\overline{V_{n,in}^2} = \frac{\overline{V_{n,out}^2}}{A_v^2}$$

$$A_v = g_m R_D \text{ (neglecting } r_o) \Rightarrow$$

$$\overline{V_{n,in}^2} = \left[ 4KT \left(\frac{2}{3}\right) g_m + \frac{K_1}{C_{ox} W L} \cdot \frac{1}{f} g_m^2 + \frac{4KT}{R_D} \right] R_D^2 \cdot \frac{1}{g_m^2 R_D^2}$$

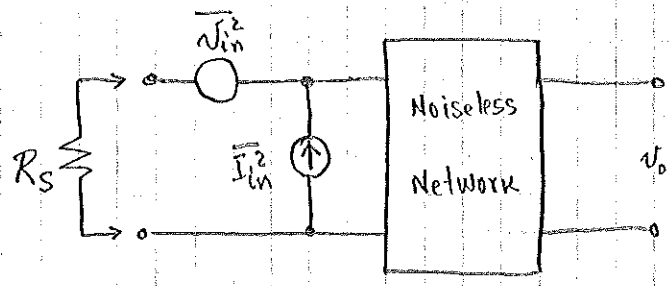
$$= \frac{8KT}{3g_m} + \frac{K_1}{C_{ox} W L f} + \frac{4KT}{g_m^2 R_D} = 4KT \left( \frac{2}{3g_m} + \frac{1}{g_m^2 R_D} \right) + \frac{K_1}{C_{ox} W L f}$$

NOTES:

- The equivalent input noise represents the minimum detectable signal of a circuit for an acceptable SNR
- The EIN is a mathematical model. Cannot be measured
- Modeling the EIN using a single voltage source produces an incomplete model. It would imply that noise is reduced if the source or input impedances are increased: wrong!
- A better model uses a series voltage source  $\overline{V_{in}^2}$  and a parallel current source  $\overline{I_{in}^2}$  in the input port, considering the correlation between both.

22-141 50 SHEETS  
 22-142 100 SHEETS  
 22-144 200 SHEETS

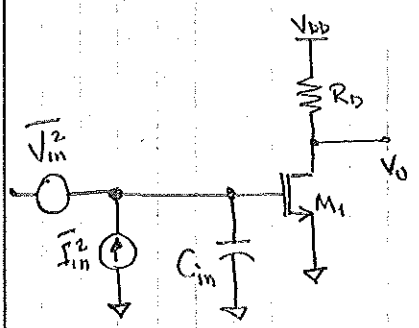
To compute  $\overline{V_{in}^2}$  and  $\overline{I_{in}^2}$  consider the extreme cases:  $R_s=0$  &  $R_s=\infty$



- 1) Represent the circuit with noise generators and EIG
- 2)  $R_s=0$ : Short-circuit the input of both representations, compute  $V_o$  and equate to find  $V_{in}$
- 3)  $R_s=\infty$ : Open-circuit both circuit inputs, compute  $V_o$  and equate to find  $I_{in}$

- When  $R_s=0$ , the short-ckt cancels  $\overline{I_{in}^2}$  and only  $\overline{V_{in}^2}$  contributes to  $\overline{V_o^2}$
- When  $R_s=\infty$ ,  $\overline{V_{in}^2}$  has no effect and only  $\overline{I_{in}^2}$  affects  $\overline{V_o^2}$ .

Example: Equivalent Noise Generators for CS amplifier with input impedance  $C_{in}$



$$\overline{V_{in}^2} = 4KT \left( \frac{2}{3} g_m \right) + \frac{K_1}{C_{ox} W L f} + \frac{4KT}{g_m^2 R_D}$$

(From previous example)

With  $R_s = \infty$ ,  $V_{gs} = I_{in} \cdot Z_c = I_{in} \left( \frac{1}{j\omega C} \right)$ ;  $V_o = V_{gs} g_m R_D$

Thus  $\overline{V_{nout}^2} = \overline{I_{in}^2} \left( \frac{1}{\omega C_{in}} \right)^2 g_m^2 R_D^2$

Equating the output noise

$\overline{V_{in}^2} \cdot g_m^2 R_D^2 = \overline{V_o^2}$  ← Taken from previous example

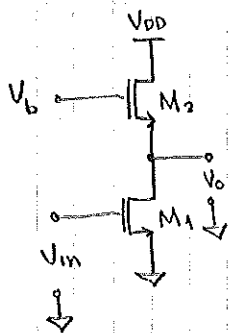
$$\overline{I_{in}^2} \left( \frac{1}{\omega C_{in}} \right)^2 g_m^2 R_D^2 = \left( 4KT \left( \frac{2}{3} g_m \right) + \frac{K_1}{C_{ox} W L} \cdot \frac{1}{f} g_m^2 + \frac{4KT}{R_D} \right) R_D^2$$

$$\overline{I_{in}^2} = \left( \frac{\omega C_{in}}{g_m} \right)^2 \left[ \frac{8KT g_m}{3} + \frac{K_1 g_m^2}{C_{ox} W L f} + \frac{4KT}{R_D} \right]$$

The  $E_{ING}$  of a mosfet suggests that  $g_m \uparrow$  reduces the noise in the output.  
(Amplifier application)

Reducing  $\bar{I}_n^2$  in the output achieved by  $g_m \downarrow$  (Current source applic.)

Analyze this:



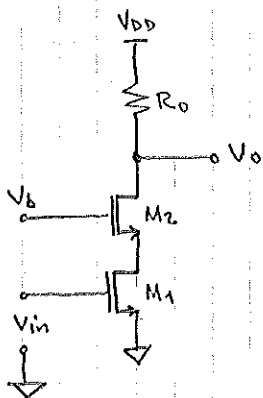
Considering only thermal noise.  
 $M_2 \rightarrow$  current source } Both work saturated  
 $M_1 \rightarrow$  Amplifier

$$\bar{V}_{n_{out}}^2 = 4KT \left( \frac{2}{3} g_{m1} + \frac{2}{3} g_{m2} \right) (r_{o1} \parallel r_{o2})^2$$

The equivalent input noise: (divide by  $A_v^2 = g_{m1}^2 (r_{o1} \parallel r_{o2})^2$ )

$$\bar{V}_{n_{in}}^2 = 4KT \left( \frac{2}{3g_{m1}} + \frac{2g_{m2}}{3g_{m1}^2} \right) \quad \text{Note how to reduce } \bar{V}_{n_{in}}^2$$

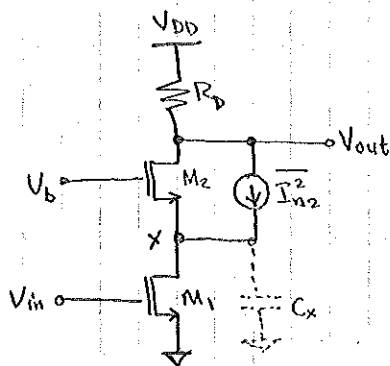
Consider a cascode connection:



$$\bar{V}_{n_{in}}^2 |_{M_2, R_D} = 4KT \left( \frac{2}{3g_{m1}} + \frac{1}{g_{m1}^2 R_D} \right) \quad (\text{Ignoring } \frac{1}{4})$$

The noise effect of  $M_2$  (thermal only)

• At low frequencies is negligible



Note that for  $V_{in} = 0$   
 $I_{n2} + I_{D2} = 0$   
 So  $M_2$  has no effect on  $V_{n,out}$

• At high frequencies we have to consider  $C_x = C_{as2} + C_{GD1}$

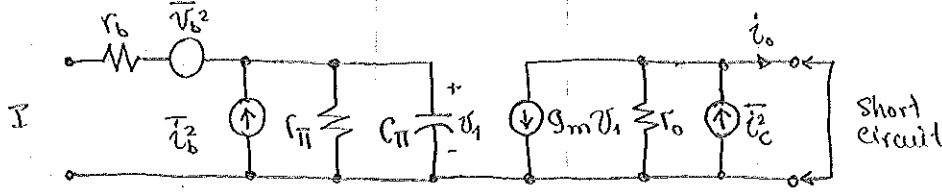
• The gain experienced by the noise:

$$\frac{V_{n,out}}{V_{n2}} \approx \frac{-R_D}{\frac{1}{g_{m2}} + \frac{1}{j\omega C_x}}$$

•  $C_x$  varies multiplying the noise of  $M_2$  and shunting the signal current of  $M_1$

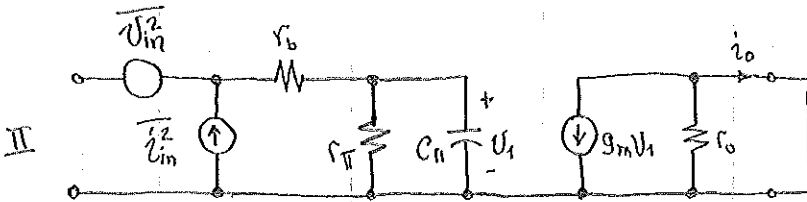


Consider a bipolar transistor:



Model neglects the effect of  $C_\mu$  and short circuits the output for max  $i_o$

The equivalent EIG circuit



1) Short-circuiting input and equating  $i_o$  in both circuits

$$\begin{aligned} \text{I: } i_o &= g_m v_1 + i_c \quad \text{assuming } r_b \ll r_\pi, v_1 = v_b \\ \text{II: } i_o &= g_m v_1 \quad \text{assuming } r_b \ll r_\pi, v_1 = v_{in} \end{aligned} \quad \left. \vphantom{\begin{aligned} \text{I: } i_o &= g_m v_1 + i_c \\ \text{II: } i_o &= g_m v_1 \end{aligned}} \right\} g_m v_b + i_c = g_m v_{in}$$

Thus  $v_{in} \approx v_b + i_c/g_m$  ← note that  $r_b$  small cancels  $i_b^2$

Assuming independence:  $v_{in}^2 = v_b^2 + i_c^2/g_m^2$   $I_c = \frac{2KT}{q} g_m$ ?

$v_b^2 = 4KT r_b$ , and  $i_c^2 = 2q I_c \Rightarrow v_{in}^2 = 4KT \left( r_b + \frac{1}{2g_m} \right)$

Term  $(r_b + 1/2g_m)$  represents the "Equivalent input noise resistance"

$r_b$  ← Physical base resistance;  $1/2g_m$  ← Effect of  $i_c$  referred to the input.

2) Open-ckt input and equate  $i_o$ :  $\beta(j\omega) i_i = i_c + \beta(j\omega) i_b$

So  $i_i = i_b + \frac{i_c}{\beta(j\omega)} \Rightarrow \overline{i_i^2} = \overline{i_b^2} + \frac{\overline{i_c^2}}{|\beta(j\omega)|^2}$  (\*)

$\beta(j\omega) = \frac{\beta_0}{1 + j\frac{\omega}{\omega_\beta}}$ ,  $\omega_\beta = \frac{1}{\beta_0} \frac{g_m}{C_\pi + C_\mu}$

Thus, replacing  $\overline{i_b^2}$  &  $\overline{i_c^2}$  into (\*)  $\overline{i_i^2} = 2q \left[ I_B + K_1 \frac{I_B^2}{f} + \frac{I_c}{|\beta(j\omega)|^2} \right]$

where  $K_1 = \frac{k_1}{2q}$  and burst noise has been excluded

$I_B \rightarrow$  Base current;  $K_1 \frac{I_B^2}{f} \rightarrow$  flicker in  $I_B$ ;  $\frac{I_c}{|\beta(j\omega)|^2} \rightarrow I_c$  noise referred to input.

See §11.5.1 for additional details

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